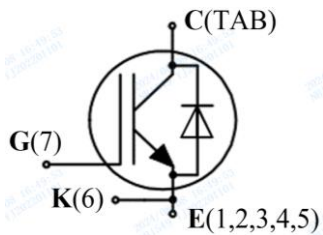


IGBT Discrete

V_{CE}	1200	V
I_C	15	A
$V_{CE(SAT)} I_C=15A$	1.55	V

Circuit



Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Features

- Low $V_{CE(sat)}$ Trench-FS IGBT technology
- Maximum junction temperature 175°C
- Positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- High short circuit capability(10us)

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	1200	V
DC Collector Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_C	30 15	A
Diode Forward Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_F	30 15	A
Continuous Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage ($t_p \leq 10\mu s, D < 0.010$)	V_{GE}	± 30	V
Turn off Safe Operating Area $V_{CE} \leq 1200V$, $T_j \leq 150^{\circ}C$		60	A
Pulsed Collector Current, $V_{GE}=15V$, t_p limited by T_{jmax}	I_{CM}	60	A
Diode Pulsed Current, t_p limited by T_{jmax}	I_{Fpuls}	60	A
Short Circuit Withstand Time, $V_{GE}=15V, V_{CC}=600V, V_{CEM} \leq 1200V$	T_{sc}	10	μs
Power Dissipation, $T_j=175^{\circ}C, T_C=25^{\circ}C$	P_{tot}	153	W



Operating Junction Temperature	T_j	-40...+175	°C
Storage Temperature	T_s	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	1200		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA$	5.2	5.8	6.4	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=15A$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$		1.55 1.80 1.90	2.05	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$			0.25 5.00	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}= \pm 20V$			100	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	-	1.72	-	nF
Reverse Transfer Capacitance	C_{res}		-	0.02	-	
Gate Charge	Q_G	$V_{CC}=600V, I_C=15A,$ $V_{GE}=15V$	-	0.14	-	uC
Short Circuit Collector Current	I_{SC}	$V_{GE}=15V, t_{sc} \leq 10\mu s,$ $V_{CC}=600V, T_j \leq 150^\circ\text{C}$	-	75	-	A

**Electrical Characteristics of the Diode** ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V_F	$I_F = 15\text{A}$ $T_j = 25^\circ\text{C}$, $T_j = 125^\circ\text{C}$ $T_j = 150^\circ\text{C}$		2.20 2.05 2.00	2.60	V

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T _j = 25℃						
Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C =15A, V _{GE} = -5v~15V, R _g =20 Ω	-	54	-	ns
Rise Time	t _r		-	47	-	ns
Turn-on Energy	E _{on}		-	0.8	-	mJ
Turn-off Delay Time	t _{d(off)}		-	184	-	ns
Fall Time	t _f		-	230	-	ns
Turn-off Energy	E _{off}		-	1.1	-	mJ
Dynamic , at T _j = 125℃						
Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C =15A, V _{GE} = -5v~15V, R _g =20 Ω	-	51	-	ns
Rise Time	t _r		-	47	-	ns
Turn-on Energy	E _{on}		-	0.9	-	mJ
Turn-off Delay Time	t _{d(off)}		-	204	-	ns
Fall Time	t _f		-	331	-	ns
Turn-off Energy	E _{off}		-	1.5	-	mJ
Dynamic , at T _j = 150℃						
Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C =15A, V _{GE} = -5v~15V, R _g =20 Ω	-	50	-	ns
Rise Time	t _r		-	48	-	ns
Turn-on Energy	E _{on}		-	0.9	-	mJ
Turn-off Delay Time	t _{d(off)}		-	219	-	ns
Fall Time	t _f		-	403	-	ns
Turn-off Energy	E _{off}		-	1.6	-	mJ

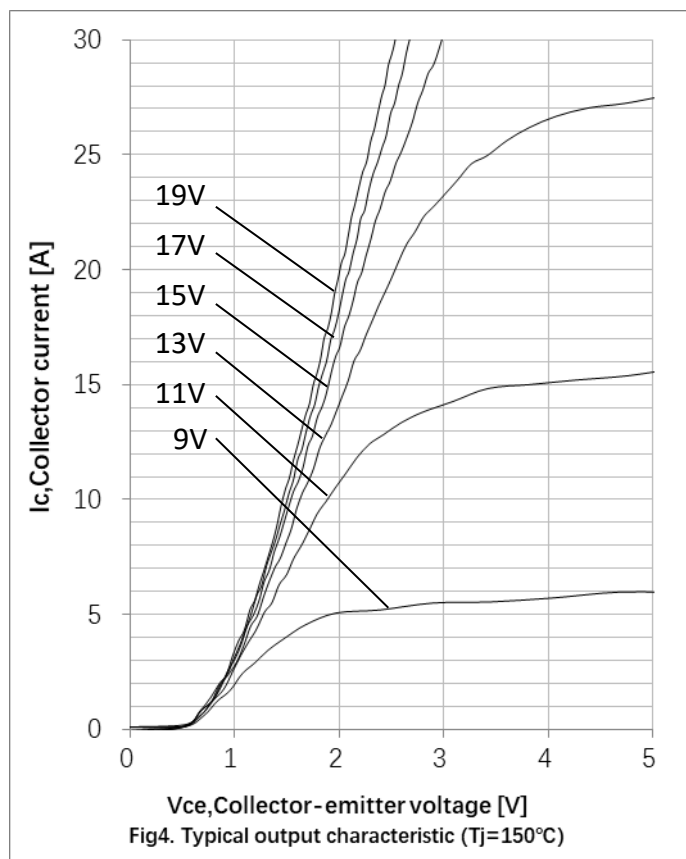
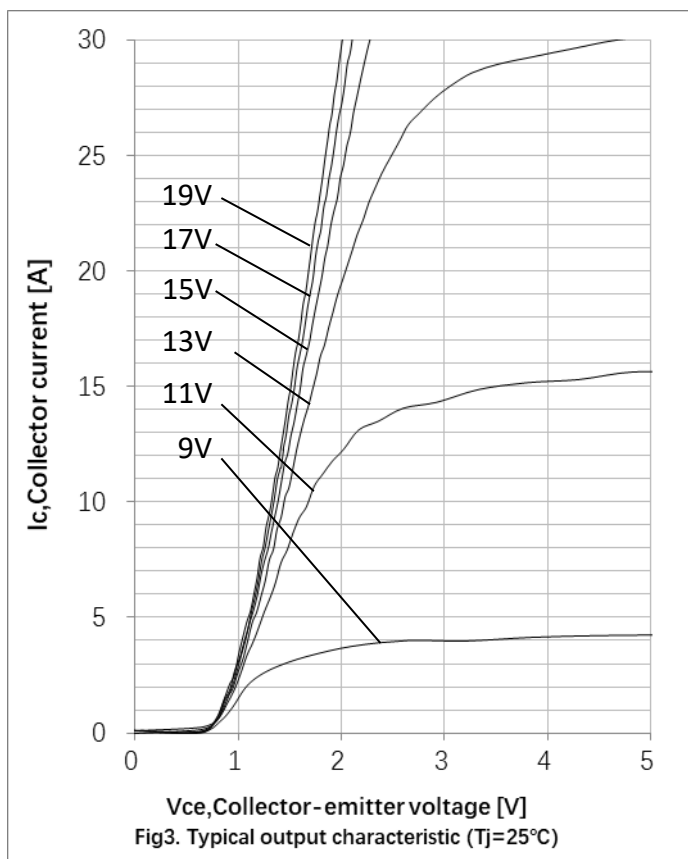
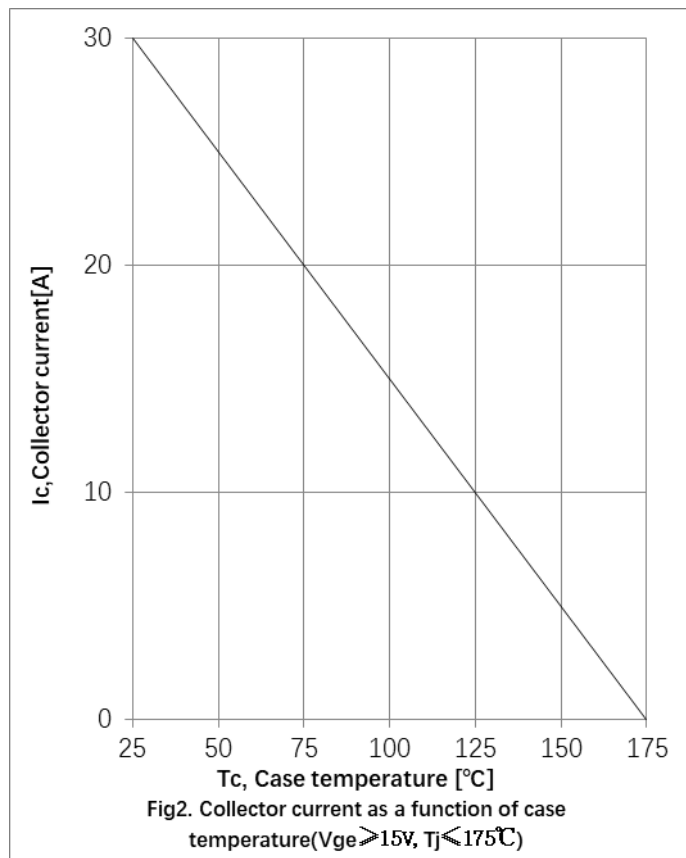
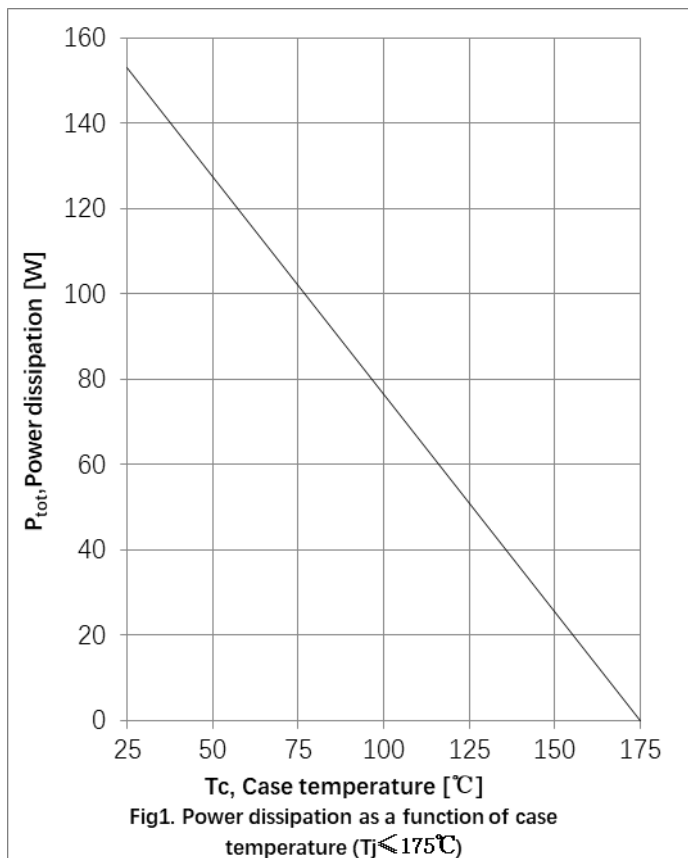


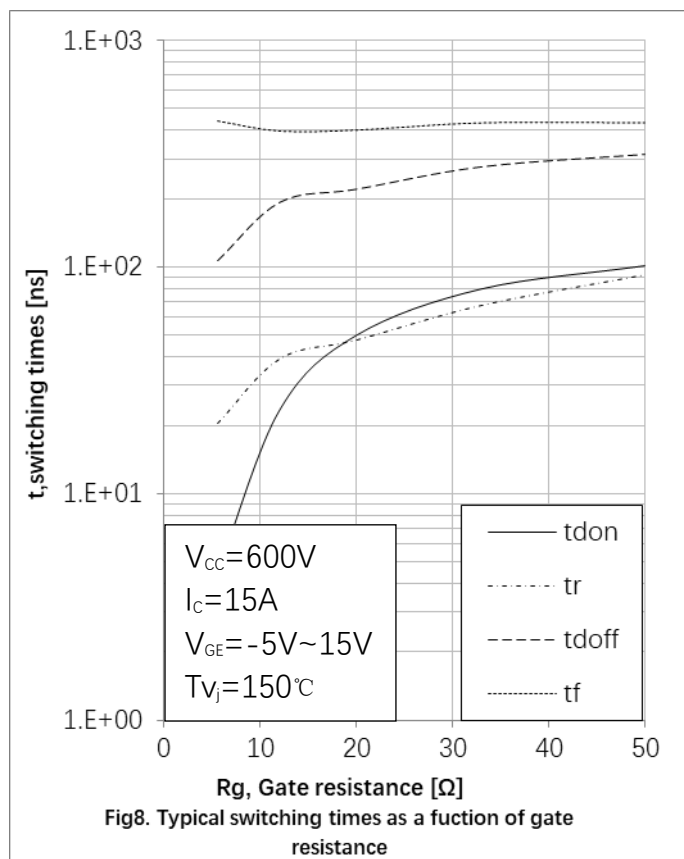
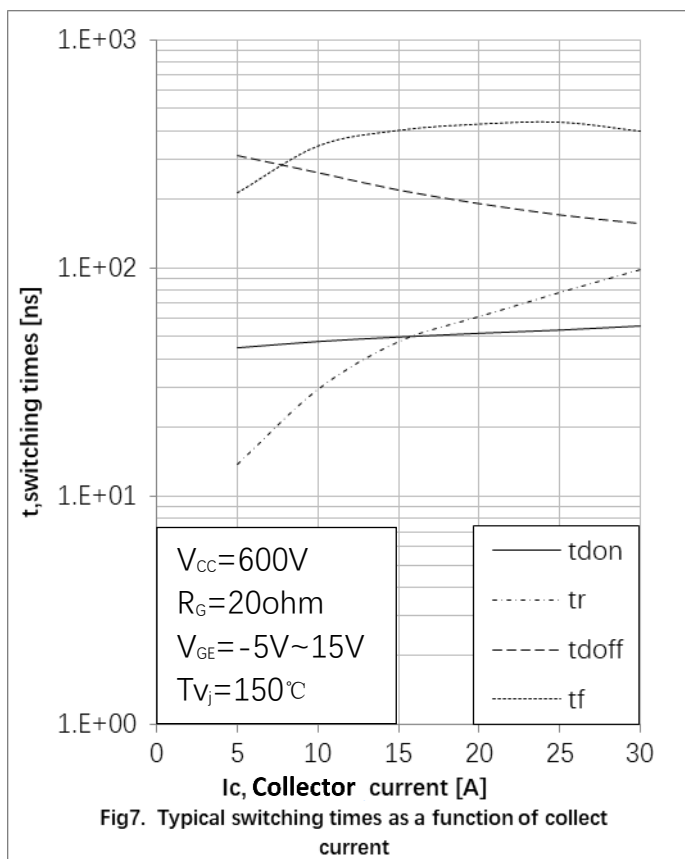
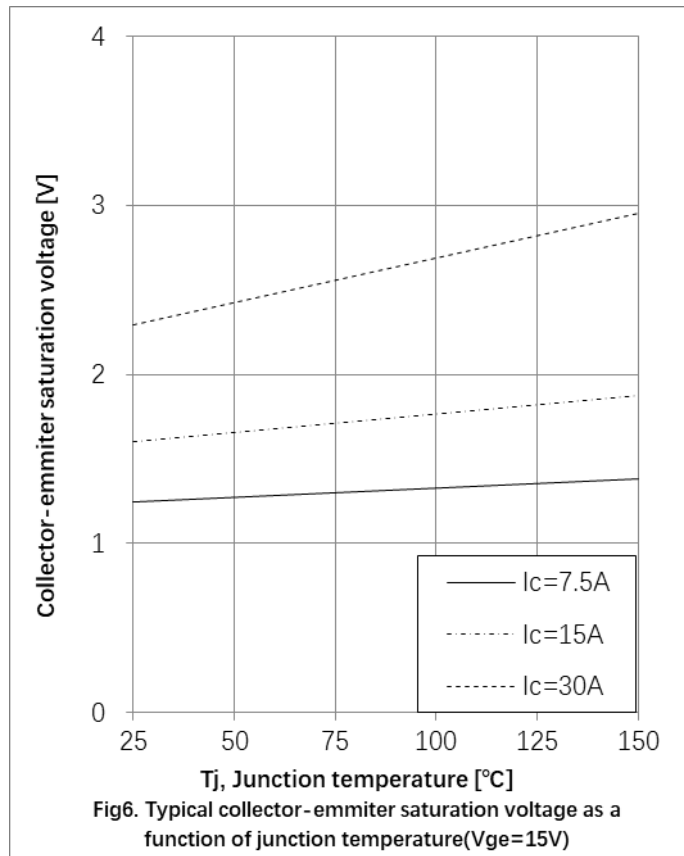
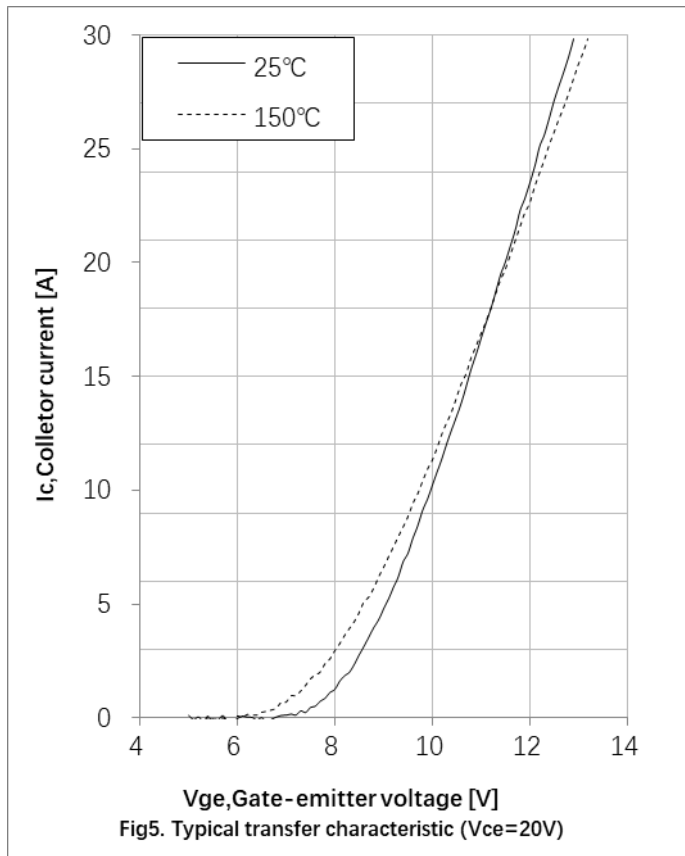
Electrical Characteristics of the DIODE

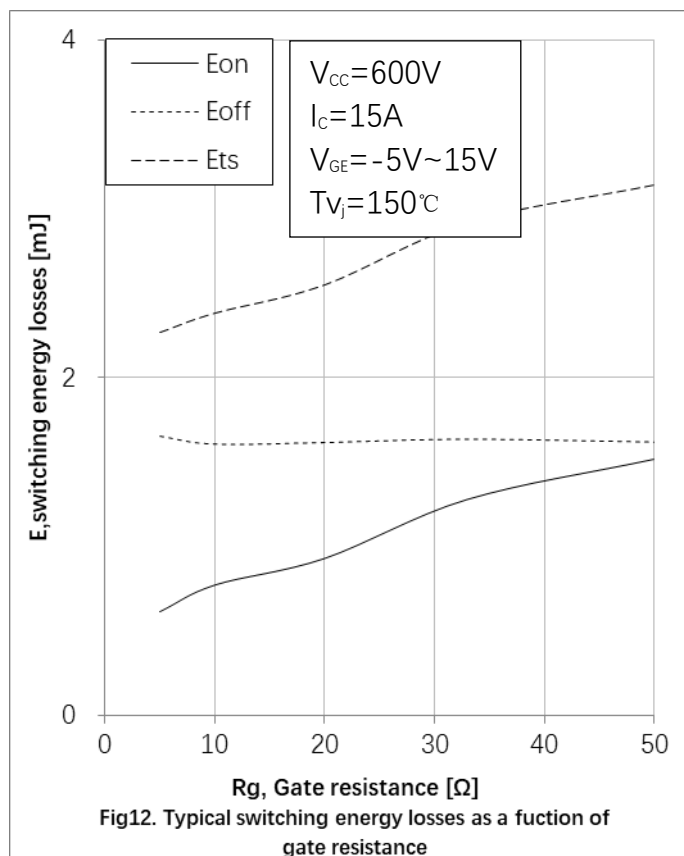
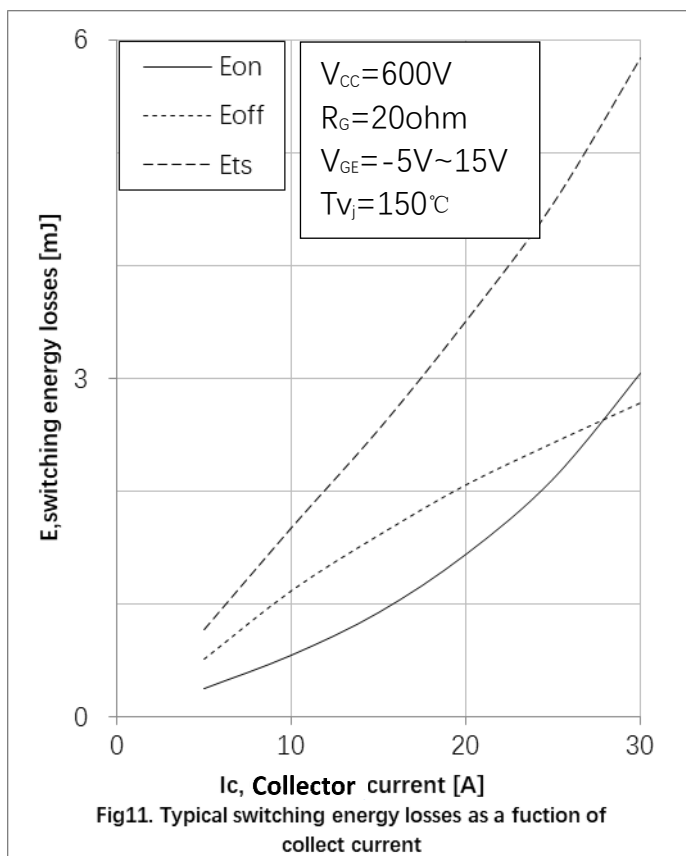
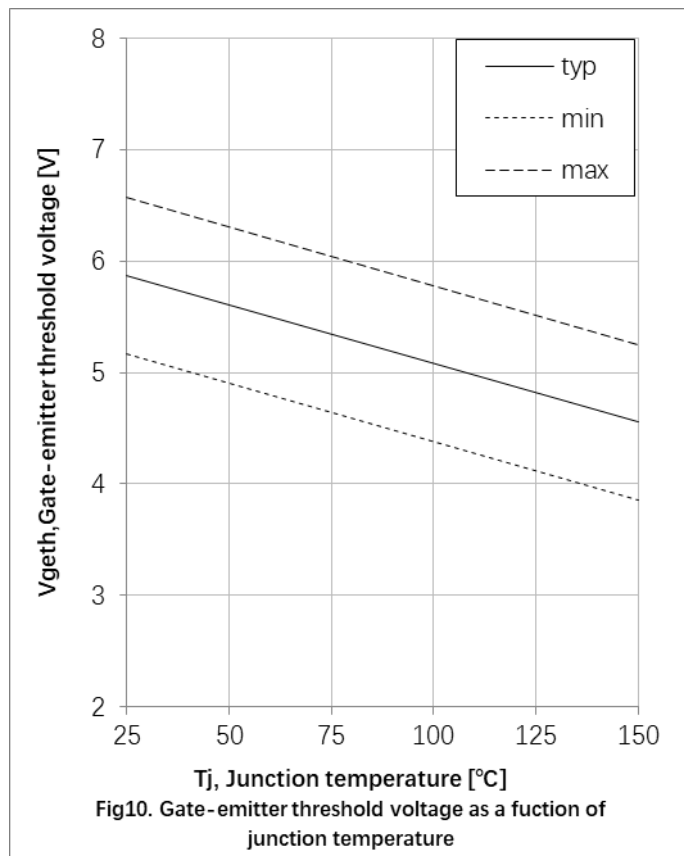
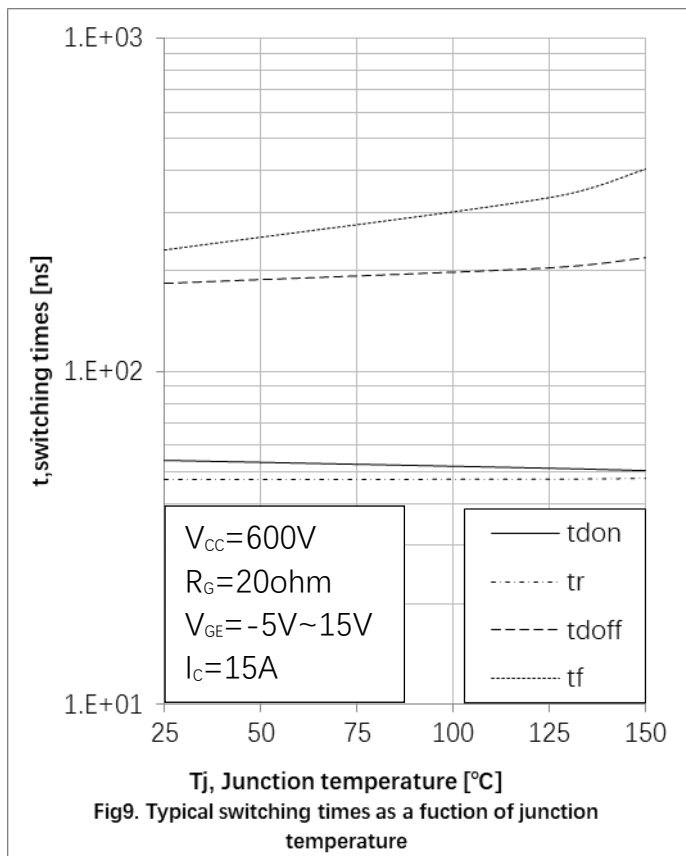
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T _j = 25°C						
Reverse Recovery Current	I _{rr}	I _F =15A, V _R =600V, -di/dt=270A/μs,	-	7.6	-	A
Reverse Recovery Time	T _{rr}		-	190	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.7	-	uC
Reverse Recovery Energy	E _{rec}		-	0.24	-	mJ
Dynamic , at T _j = 125°C						
Reverse Recovery Current	I _{rr}	I _F =15A, V _R =600V, -di/dt=270A/μs,	-	10.4	-	A
Reverse Recovery Time	T _{rr}		-	270	-	ns
Reverse Recovery Charge	Q _{rr}		-	1.3	-	uC
Reverse Recovery Energy	E _{rec}		-	0.50	-	mJ
Dynamic , at T _j = 150°C						
Reverse Recovery Current	I _{rr}	I _F =15A, V _R =600V, -di/dt=270A/μs,	-	11.6	-	A
Reverse Recovery Time	T _{rr}		-	300	-	ns
Reverse Recovery Charge	Q _{rr}		-	1.6	-	uC
Reverse Recovery Energy	E _{rec}		-	0.60	-	mJ

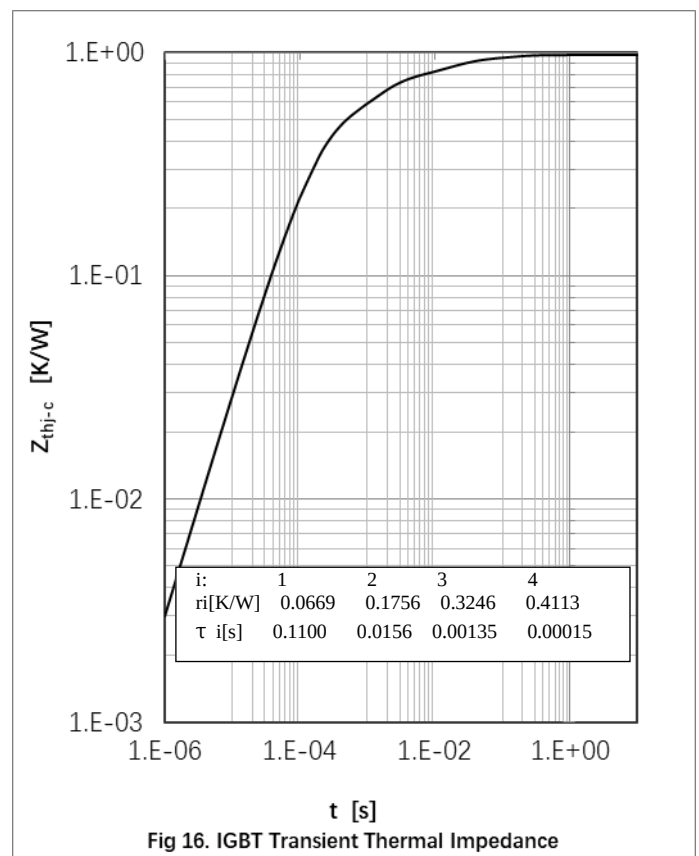
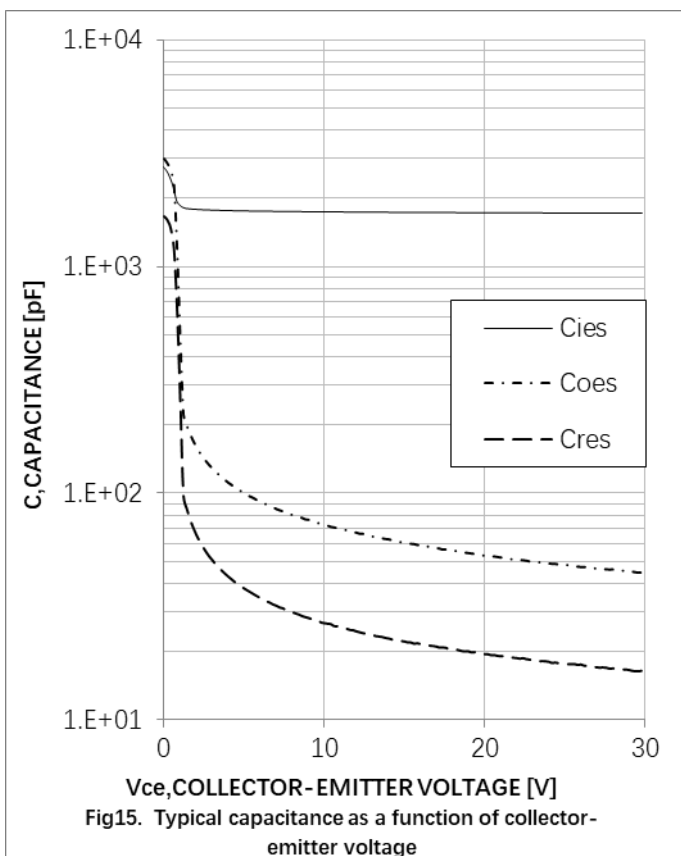
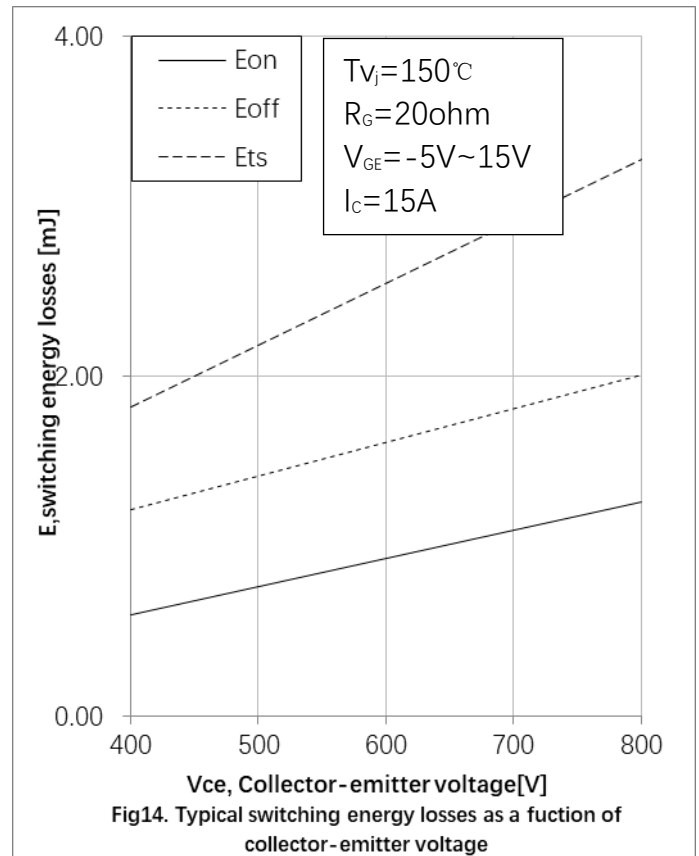
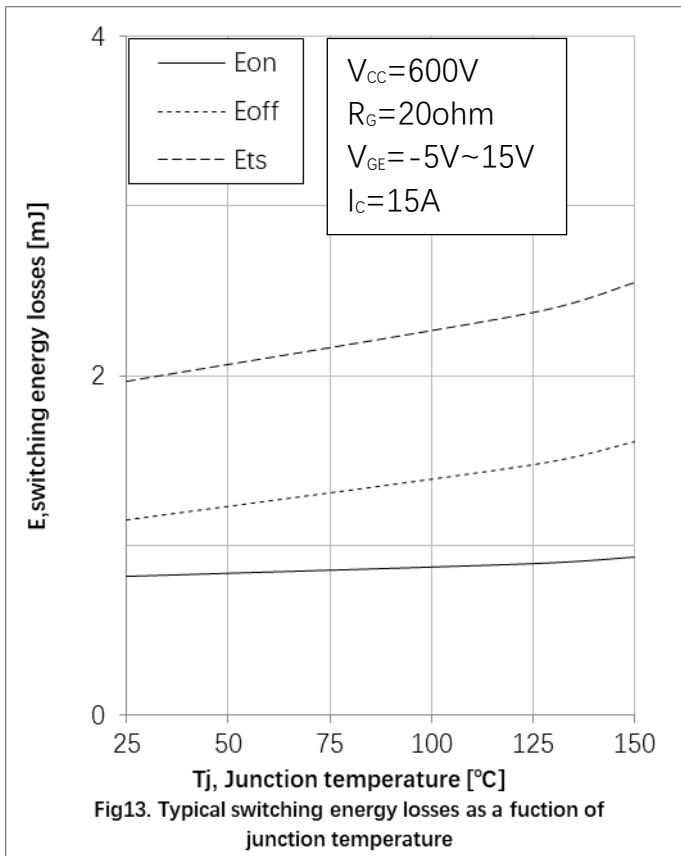
Thermal Resistance

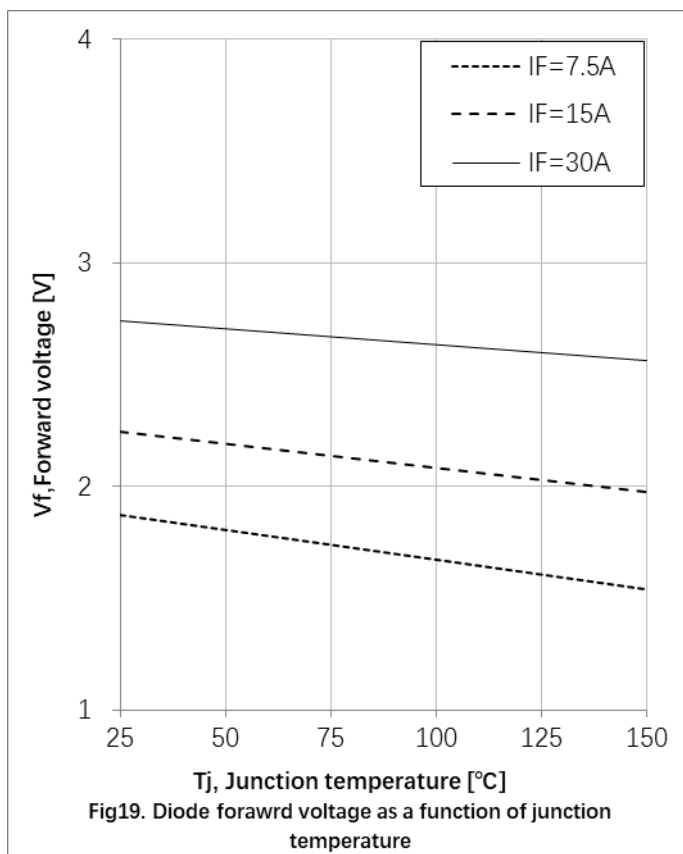
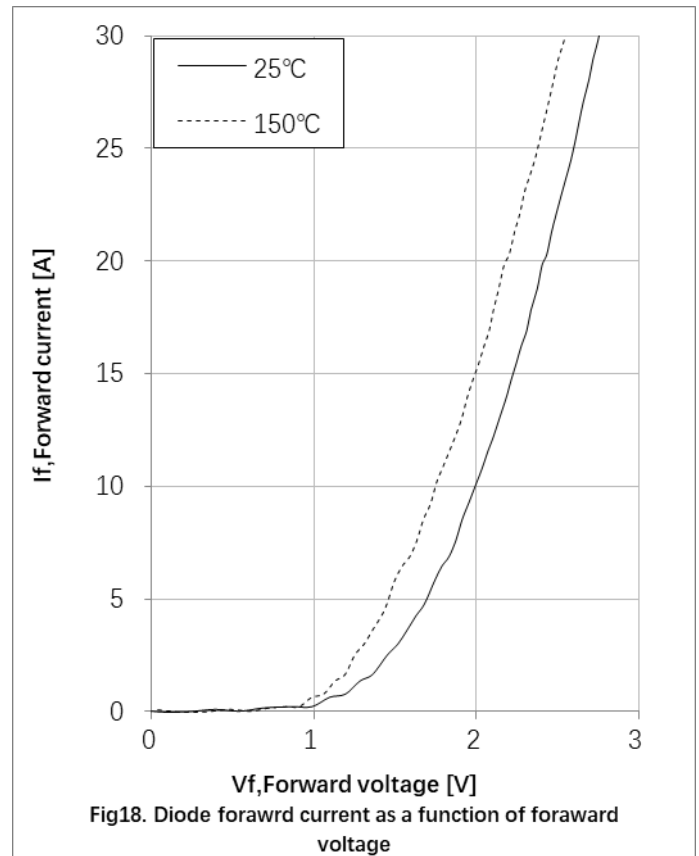
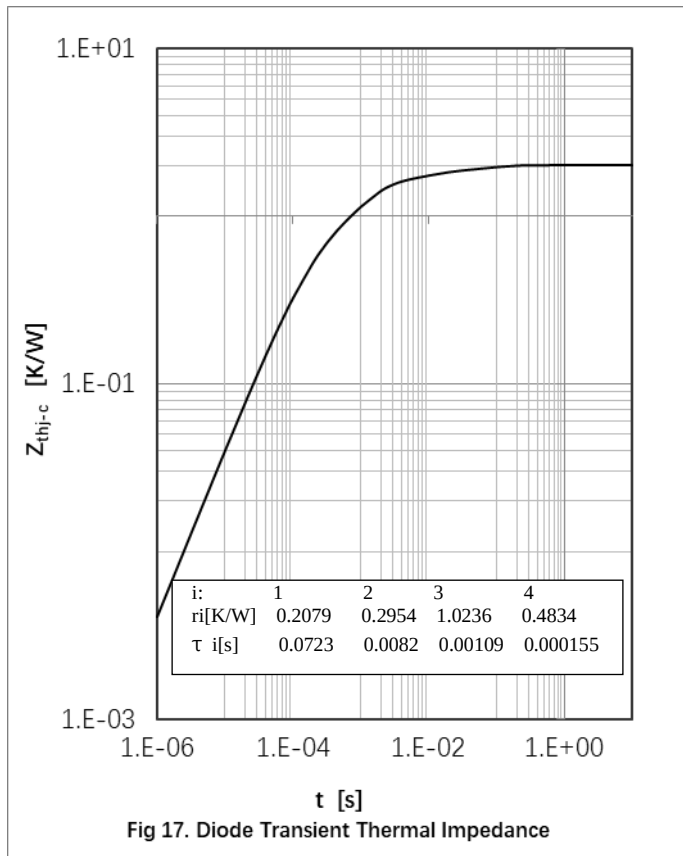
Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{th(j-c)}	1.00	K/W
Diode Thermal Resistance, Junction - Case	R _{th(j-c)}	2.00	K/W
Thermal Resistance, Junction - Ambient	R _{th(j-a)}	40	K/W



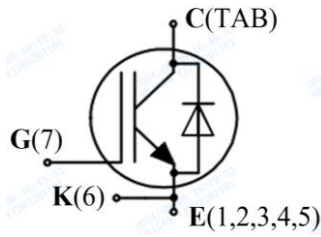






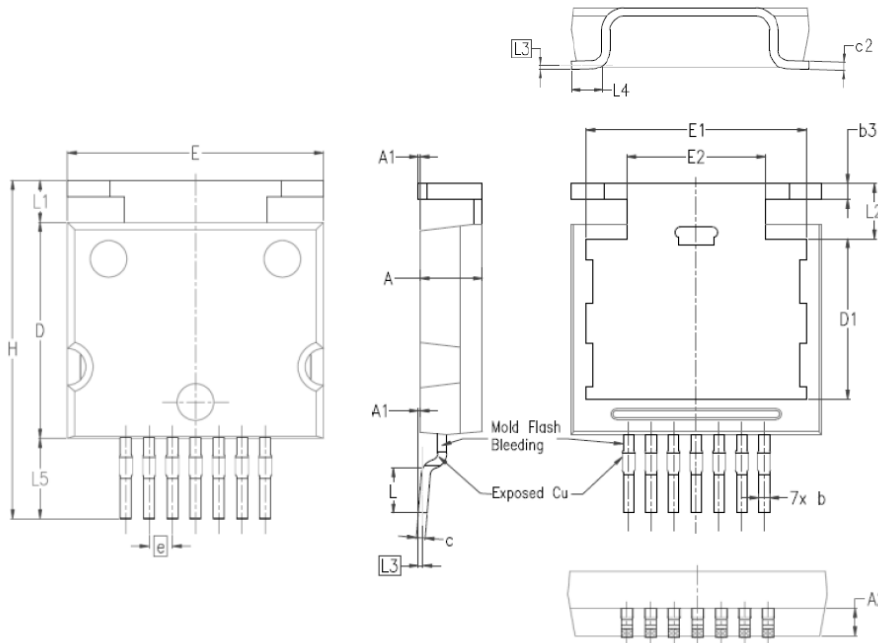


● Circuit Diagram



● Package Outline Information

CASE: T2PACK



T2PACK		
Dim	Min	Max
A	3.30	3.70
A1	---	0.25
A2	1.30	1.70
b	0.5	0.7
b3	0.8	1
c	0.4	0.6
c2	0.4	0.6
D	11.70	11.90
D1	8.80	9.20
E	13.60	14.40
E1	12.00	12.80
E2	7.60	8.00
e	1.27 BSC	
H	17.70	19.30
L	1.90	3.10
L1	2.30 REF	
L2	2.85	3.35
L3	0.25 BSC	
L4	1.25	2.45
L5	4.40REF	



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